

STGB10NC60KD, STGD10NC60KD STGF10NC60KD, STGP10NC60KD

10 A, 600 V short-circuit rugged IGBT

Features

- Lower on voltage drop (V_{CE(sat)})
- Lower C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode
- Short-circuit withstand time 10µs

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

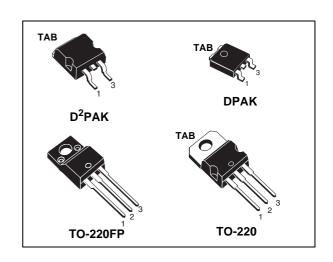


Figure 1. Internal schematic diagram

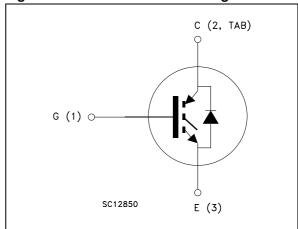


Table 1. Device summary

Order codes	Marking	Packages	Packaging
STGB10NC60KDT4	GB10NC60KD	D ² PAK	Tape and reel
STGD10NC60KDT4	GD10NC60KD	DPAK	rape and reer
STGF10NC60KD	GF10NC60KD	TO-220FP	Tube
STGP10NC60KD	GP10NC60KD	TO-220	Tube

Contents STGx10NC60KD

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STGx10NC60KD Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

			Value				
Symbol	Parameter	D²PAK TO-220	DPAK	TO-220FP	Unit		
V _{CES}	Collector-emitter voltage (V _{GE} = 0)		600		V		
I _C ⁽¹⁾	Continuous collector current at T _C = 25°C	20)	9	Α		
I _C ⁽¹⁾	Continuous collector current at T _C = 100°C	10)	6	Α		
I _{CL} ⁽²⁾	Turn-off latching current		30		Α		
I _{CP} ⁽³⁾	Pulsed collector current	30			Α		
V _{GE}	Gate-emitter voltage	±20			V		
IF	Diode RMS forward current at Tc=25°C	10			Α		
I _{FSM}	Surge non repetitive forward current $T_p = 10 \text{ ms}$ sinusoidal	20			Α		
P _{TOT}	Total dissipation at T _C = 25°C	65	62	25	W		
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T _C =25°C)	2500		2500	V		
t _{scw}	Short-circuit withstand time V_{CE} = 0.5 V_{CES} , T_j = 125 °C, R_G = 10 Ω V_{GE} = 12 V	, 10		μs			
T _{stg}	Storage temperature	- 55 to 150		°C			
T _j	Operating junction temperature			J			

^{1.} Calculated according to the iterative formula

$$I_{C}(T_{C}) = \frac{T_{j(max)} - T_{C}}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_{C}(T_{C}))}$$

- 2. Vclamp = 80 % V_{CES} , V_{GE} = 15 V, R_{G} = 10 Ω , T_{J} = 150 °C
- 3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Electrical ratings STGx10NC60KD

Table 3. Thermal data

Symbol	Parameter	TO-220 D²PAK	DPAK	TO-220FP	Unit
R _{thj-case}	Thermal resistance junction-case IGBT	1.9	2	5	
R _{thj-case}	R _{thj-case} Thermal resistance junction-case diode		4.5	7	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	62.5	100	62.5	

2 Electrical characteristics

(T_i =25°C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)CES}	Collector-emitter breakdown voltage (V _{GE} = 0)	I _C = 1mA	600			V
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 5A V _{GE} = 15V, I _C = 5A, T _j = 125°C		2.2 1.8	2.5	V V
V _{GE(th)}	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_{C} = 250\mu A$	4.5		6.5	V
I _{CES}	Collector cut-off current (V _{GE} = 0)	V _{CE} = 600 V V _{CE} =600 V, T _j = 125°C			150 1	μA mA
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	V _{GE} = ±20V			±100	nA
9 _{fs} ⁽¹⁾	Forward transconductance	$V_{CE} = 15V_{,} I_{C} = 5A$		15		S

^{1.} Pulse test: pulse duration < 300 μ s, duty cycle < 2 %

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{CE} = 25V, f = 1MHz,$ $V_{GE} = 0$	-	380 46 8.5	-	pF pF pF
Q _g Q _{ge} Q _{gc}	Total gate charge Gate-emitter charge Gate-collector charge	$V_{CE} = 390V$, $I_{C} = 5A$, $V_{GE} = 15V$, (see Figure 19)	1	19 5 9	-	nC nC nC

Electrical characteristics STGx10NC60KD

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω , V_{GE} = 15V (see Figure 20)	-	17 6 655	-	ns ns A/µs
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω V_{GE} = 15V, T_{j} =125°C (see Figure 20)	-	16.5 6.5 575	-	ns ns A/µs
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390V, I_{C} = 5A, R_{GE} = 10 Ω V_{GE} = 15V (see Figure 20)	-	33 72 82	-	ns ns ns
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390V, I_{C} = 5A, R_{GE} =10 Ω V_{GE} =15V, T_{j} =125°C (see Figure 20)	-	60 106 136	-	ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
E _{on} ⁽¹⁾ E _{off} ⁽²⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω , V_{GE} =15V (see Figure 20)	-	55 85 140	-	μJ μJ μJ
E _{on} ⁽¹⁾ E _{off} ⁽²⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω , V_{GE} = 15V, T_{j} = 125°C (see Figure 20)	-	87 162 249	-	μJ μJ μJ

Eon is the tun-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)

^{2.} Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

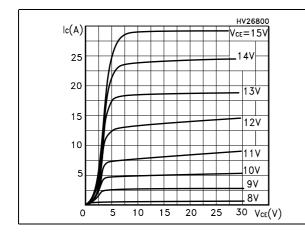
Symbol	Parameter	Test conditions	Min	Тур.	Max.	Unit
V _F	Forward on-voltage	I _F =5 A I _F =5 A, T _j =125 °C	-	2 1.6	-	V V
t _{rr} Q _{rr} I _{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _F =5 A, V _R =40 V, di/dt=100 A/μs (see <i>Figure 5</i>)	-	22 14 1.3	-	ns nC A
t _{rr} Q _{rr} I _{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_F =5 A, V_R =40 V, T_j =125 °C, di/dt=100 A/ μ s (see <i>Figure 5</i>)	-	35 40 2.2		ns nC A

Electrical characteristics STGx10NC60KD

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

Figure 3. Transfer characteristics



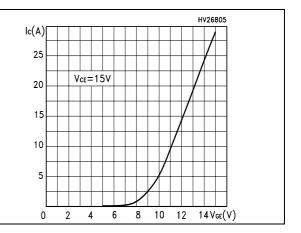
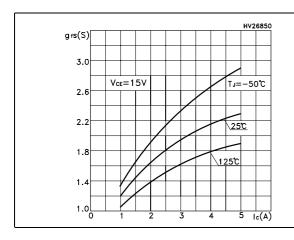


Figure 4. Transconductance

Figure 5. Collector-emitter on voltage vs temperature



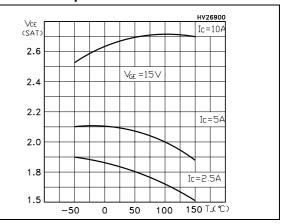
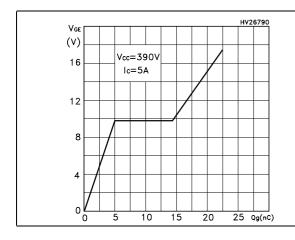
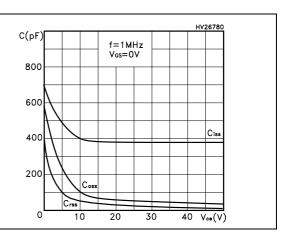


Figure 6. Gate charge vs gate-source voltage Figure 7. Capacitance variations





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Figure 8. Normalized gate threshold voltage Figure 9. Collector-emitter on voltage vs vs temperature collector current

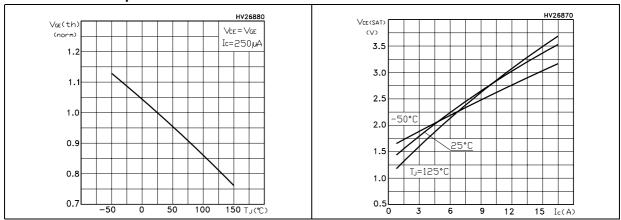


Figure 10. Normalized breakdown voltage vs Figure 11. Switching losses vs temperature temperature

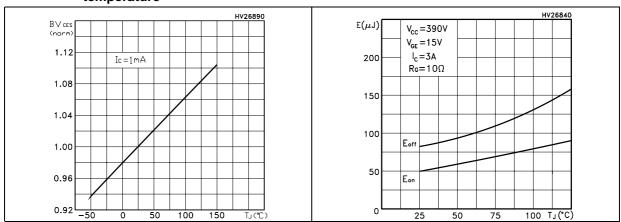
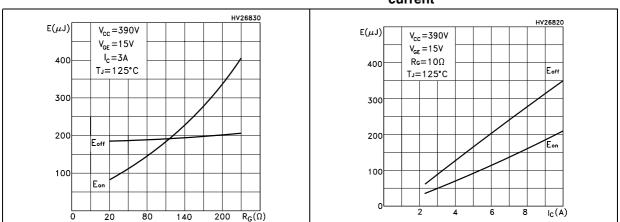


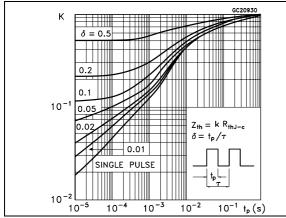
Figure 12. Switching losses vs gate resistance Figure 13. Switching losses vs collector current



Electrical characteristics STGx10NC60KD

Figure 14. Thermal impedance for D²PAK, DPAK and TO-220

Figure 15. Turn-off SOA



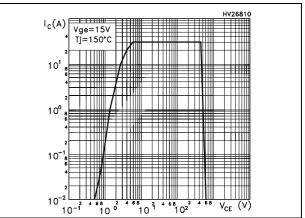
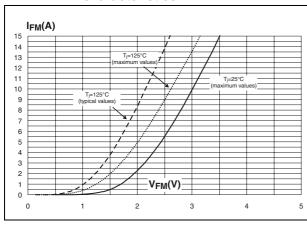
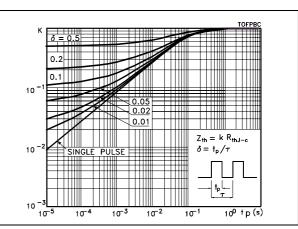


Figure 16. Emitter-collector diode characteristics

Figure 17. Thermal impedance for TO-220FP





STGx10NC60KD Test circuits

3 Test circuits

Figure 18. Test circuit for inductive load switching

Figure 19. Gate charge test circuit

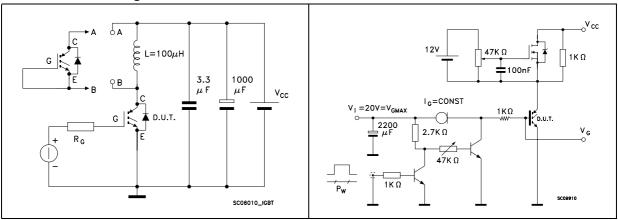
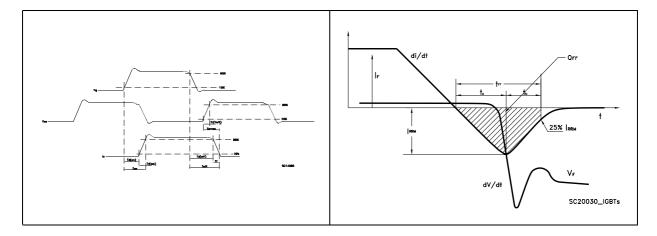


Figure 20. Switching waveform

Figure 21. Diode recovery time waveform



4 Package mechanical data

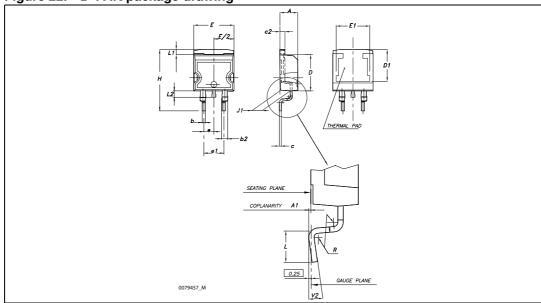
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

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Table 9. D²PAK package mechanical data

D.		mm			inch			
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	4.40		4.60	0.173		0.181		
A1	0.03		0.23	0.001		0.009		
b	0.70		0.93	0.027		0.037		
b2	1.14		1.70	0.045		0.067		
С	0.45		0.60	0.017		0.024		
c2	1.23		1.36	0.048		0.053		
D	8.95		9.35	0.352		0.368		
D1	7.50			0.295				
E	10		10.40	0.394		0.409		
E1	8.50			0.334				
е		2.54			0.1			
e1	4.88		5.28	0.192		0.208		
Н	15		15.85	0.590		0.624		
J1	2.49		2.69	0.099		0.106		
L	2.29		2.79	0.090		0.110		
L1	1.27		1.40	0.05		0.055		
L2	1.30		1.75	0.051		0.069		
R		0.4			0.016			
V2	0°		8°	0°		8°		

Figure 22. D²PAK package drawing



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Table 10. DPAK package mechanical data

D!	mm					
Dim.	Min.	Тур	Max.			
Α	2.20		2.40			
A1	0.90		1.10			
A2	0.03		0.23			
b	0.64		0.90			
b4	5.20		5.40			
С	0.45		0.60			
c2	0.48		0.60			
D	6.00		6.20			
D1		5.10				
Е	6.40		6.60			
E1		4.70				
е		2.28				
e1	4.40		4.60			
Н	9.35		10.10			
L	1					
L1		2.80				
L2		0.80				
L4	0.60		1			
R		0.20				
V2	0 °		8 °			

Figure 23. DPAK package drawing

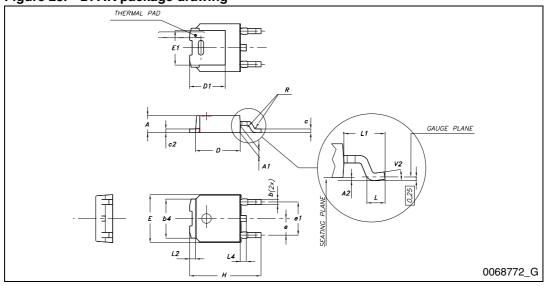
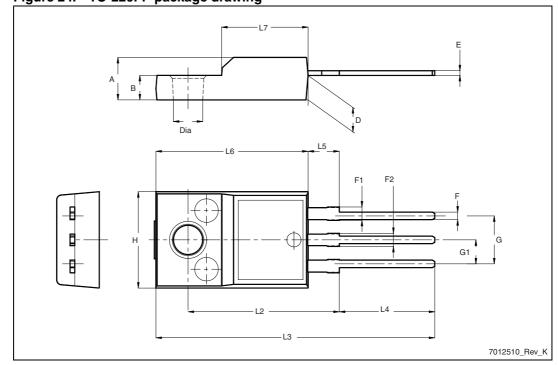


Table 11. TO-220FP package mechanical data

D:		mm					
Dim.	Min.	Тур.	Max.				
А	4.4		4.6				
В	2.5		2.7				
D	2.5		2.75				
Е	0.45		0.7				
F	0.75		1				
F1	1.15		1.70				
F2	1.15		1.70				
G	4.95		5.2				
G1	2.4		2.7				
Н	10		10.4				
L2		16					
L3	28.6		30.6				
L4	9.8		10.6				
L5	2.9		3.6				
L6	15.9		16.4				
L7	9		9.3				
Dia	3		3.2				

Figure 24. TO-220FP package drawing

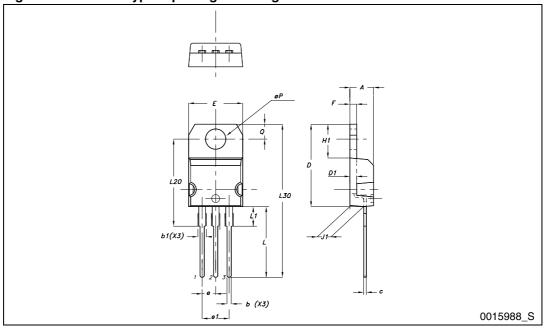


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Table 12. TO-220 type A mechanical data

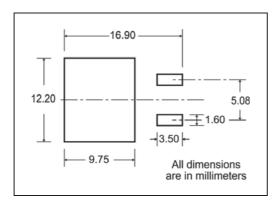
Dim.	mm		
	Min.	Тур.	Max.
Α	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 25. TO-220 type A package drawing

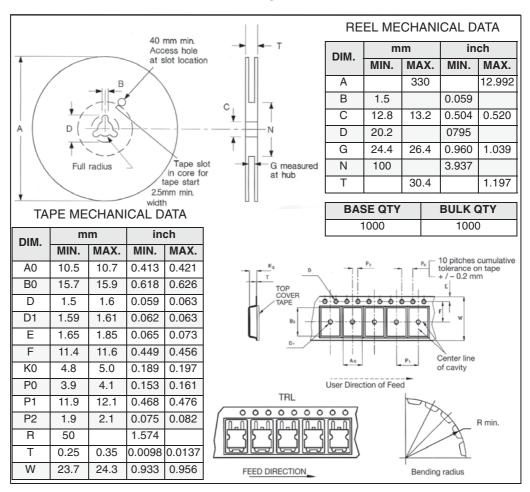


5 Packaging mechanical data

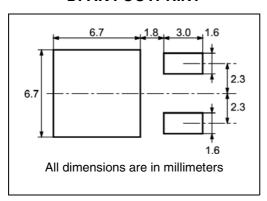
D²PAK FOOTPRINT



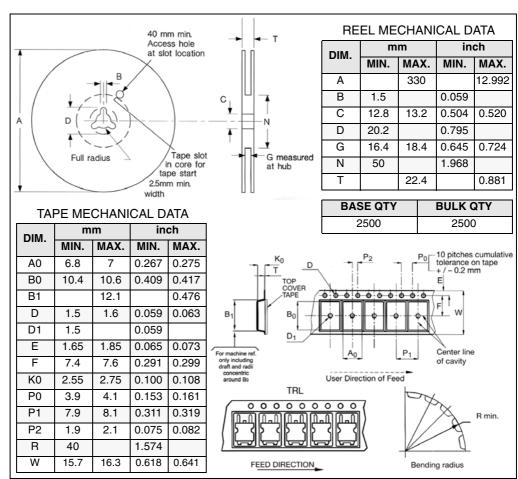
TAPE AND REEL SHIPMENT



DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



STGx10NC60KD Revision history

6 Revision history

Table 13. Document revision history

Date	Revision	Changes	
14-Jun-2005	1	New release.	
19-Jul-2005	2	Complete version.	
27-Jan-2006	3	Inserted ecopack indication.	
01-Mar-2006	4	The document has been reformatted.	
08-Feb-2007	5	Modified value on Table 6.: Switching on/off (inductive load).	
24-Nov-2009	6	Inserted DPAK package option.	

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